



preliminary

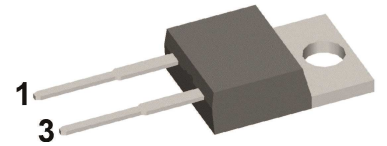
Sonic Fast Recovery Diode

V_{RRM}	=	1200 V
I_{FAV}	=	10 A
t_{rr}	=	200 ns

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Single Diode

Part number

DHG10I1200PA



Backside: cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm}-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: TO-220

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

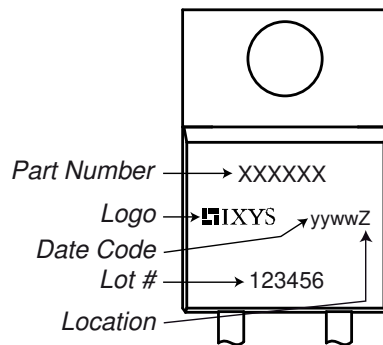
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Fast Diode				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
I_R	reverse current, drain current	$V_R = 1200 V$	$T_{VJ} = 25^{\circ}C$		15	μA	
		$V_R = 1200 V$	$T_{VJ} = 125^{\circ}C$		0.2	mA	
V_F	forward voltage drop	$I_F = 10 A$	$T_{VJ} = 25^{\circ}C$		2.22	V	
		$I_F = 20 A$			2.93	V	
		$I_F = 10 A$	$T_{VJ} = 125^{\circ}C$		2.23	V	
		$I_F = 20 A$			3.14	V	
I_{FAV}	average forward current	$T_C = 105^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}C$		10	A	
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		1.25	V	
r_F	slope resistance				90	m Ω	
R_{thJC}	thermal resistance junction to case				1.5	K/W	
R_{thCH}	thermal resistance case to heatsink			0.5		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		85	W	
I_{FSM}	max. forward surge current	$t = 10 ms; (50 Hz), sine; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$		60	A	
C_J	junction capacitance	$V_R = 600 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		4	pF	
I_{RM}	max. reverse recovery current	} $I_F = 10 A; V_R = 600 V$ $-di_F / dt = 250 A/\mu s$	$T_{VJ} = 25^{\circ}C$		9	A	
			$T_{VJ} = 125^{\circ}C$		10.5	A	
t_{rr}	reverse recovery time		$T_{VJ} = 25^{\circ}C$		200	ns	
			$T_{VJ} = 125^{\circ}C$		350	ns	

Package TO-220			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				2		g
M_D	mounting torque		0.4		0.6	Nm
F_C	mounting force with clip		20		60	N

Product Marking

Part description

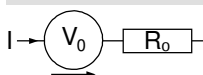
D = Diode
 H = Sonic Fast Recovery Diode
 G = extreme fast
 10 = Current Rating [A]
 I = Single Diode
 1200 = Reverse Voltage [V]
 PA = TO-220AC (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DHG10I1200PA	DHG10I1200PA	Tube	50	505273

Similar Part	Package	Voltage class
DHG10I1200PM	TO-220ACFP (2)	1200

Equivalent Circuits for Simulation

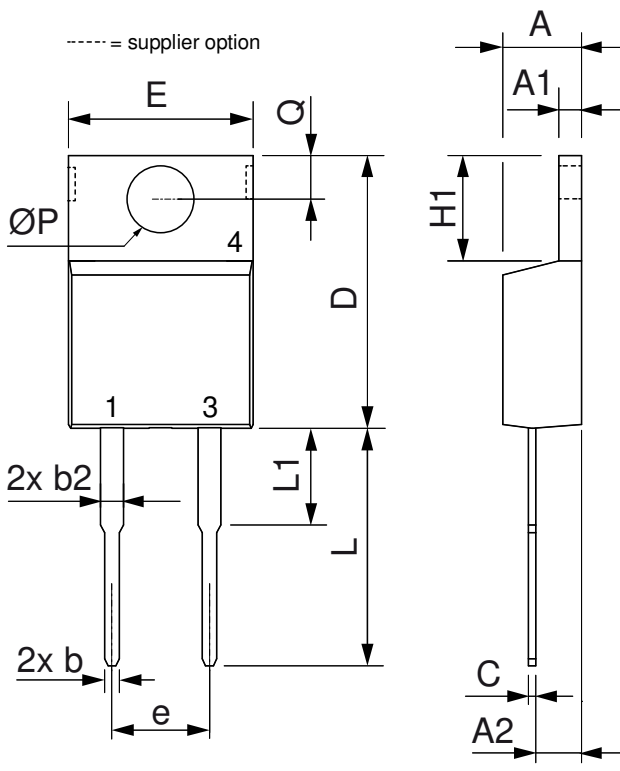
* on die level

 $T_{VJ} = 150^{\circ}\text{C}$

Fast Diode

$V_{0\ max}$	threshold voltage	1.25	V
$R_{0\ max}$	slope resistance *	87	mΩ



Outlines TO-220



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.32	4.82	0.170	0.190
A1	1.14	1.39	0.045	0.055
A2	2.29	2.79	0.090	0.110
b	0.64	1.01	0.025	0.040
b2	1.15	1.65	0.045	0.065
C	0.35	0.56	0.014	0.022
D	14.73	16.00	0.580	0.630
E	9.91	10.66	0.390	0.420
e	5.08	BSC	0.200	BSC
H1	5.85	6.85	0.230	0.270
L	12.70	13.97	0.500	0.550
L1	2.79	5.84	0.110	0.230
ØP	3.54	4.08	0.139	0.161
Q	2.54	3.18	0.100	0.125





Fast Diode

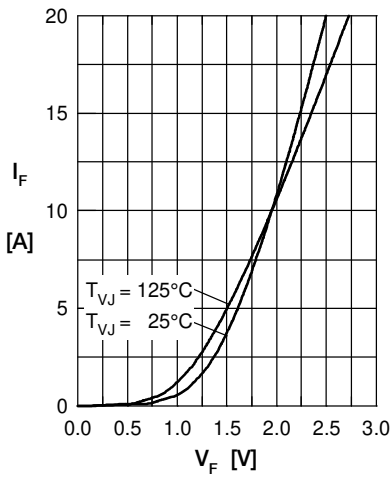


Fig. 1 Typ. Forward current versus V_F

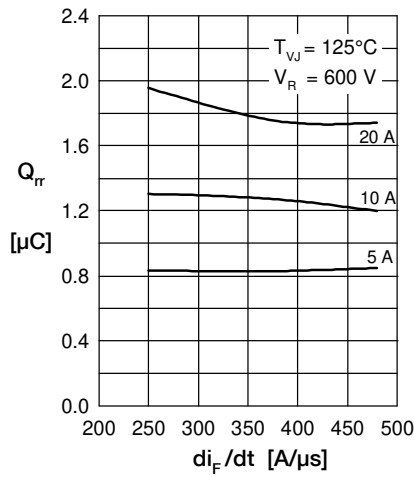


Fig. 2 Typ. reverse recov. charge Q_{rr} versus di/dt

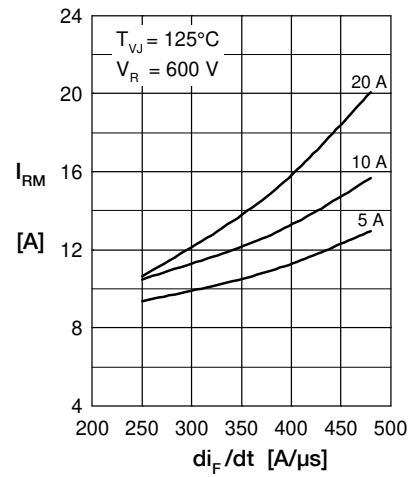


Fig. 3 Typ. peak reverse current I_{RM} versus di/dt

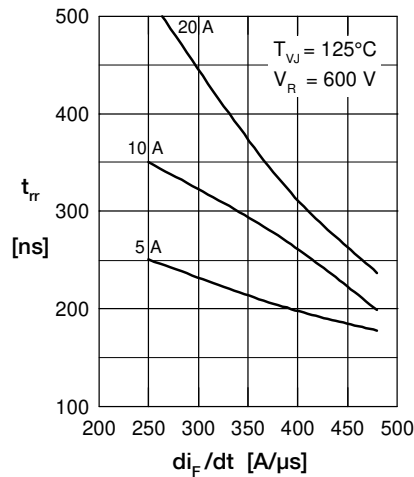


Fig. 4 Dynamic parameters Q_{rr} , I_{RM} versus T_{VJ}

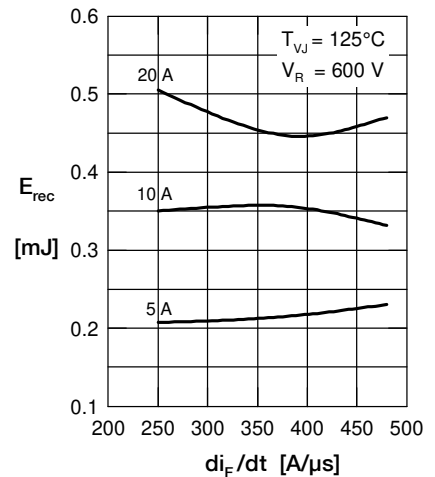


Fig. 5 Typ. recovery time t_{rr} versus di/dt

Fig. 6 Typ. recovery energy E_{rec} versus di/dt

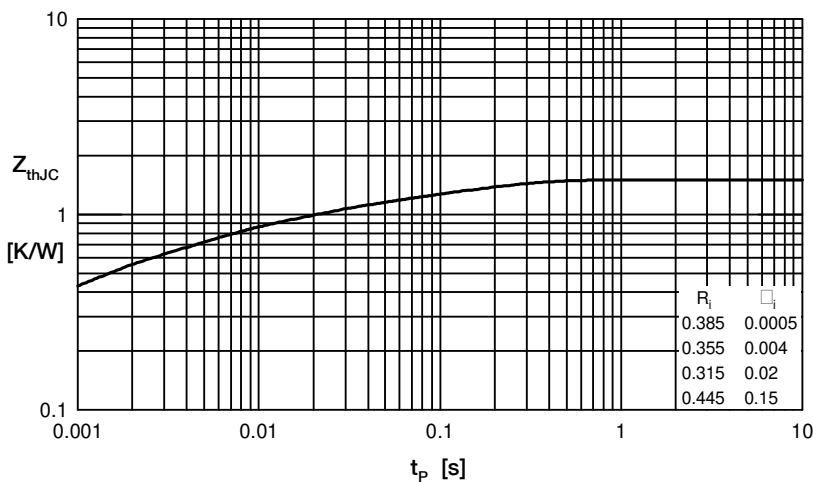


Fig. 7 Typ. transient thermal impedance junction to case